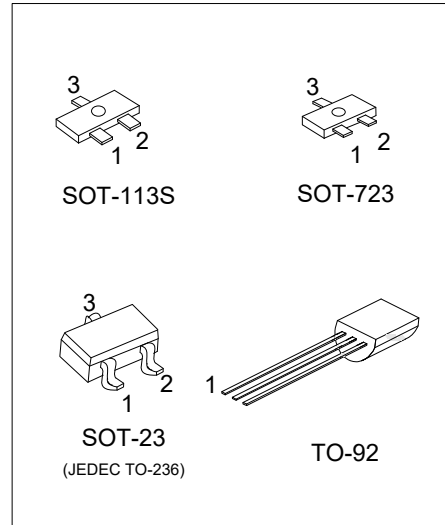




2SK303

JFET

LOW-FREQUENCY GENERAL-PURPOSE AMPLIFIER APPLICATIONS



■ **FEATURES**

- * Ideal For Potentiometers
- * Analog Switches
- * Low Frequency Amplifiers
- * Constant Current Supplies
- * Impedance Conversion

■ **ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SK303L-xx-AE3-R	2SK303G-xx-AE3-R	SOT-23	S	D	G	Tape Reel
2SK303L-xx-A3C-R	2SK303G-xx-A3C-R	SOT-113S	S	D	G	Tape Reel
2SK303L-xx-AQ3-R	2SK303G-xx-AQ3-R	SOT-723	S	D	G	Tape Reel
2SK303L-xx-T92-B	2SK303G-xx-T92-B	TO-92	G	S	D	Tape Box
2SK303L-xx-T92-K	2SK303G-xx-T92-K	TO-92	G	S	D	Bulk

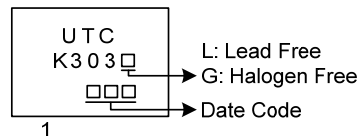
Note: Pin Assignment: S: Source D: Drain G: Gate

<p>2SK303G-xx-AE3-R</p>	<p>(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AE3: SOT-23, T92: TO-92, A3C: SOT-113S AQ3: SOT-723 (3) xx: Refer to Classification of I_{DSS} (4) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ **MARKING**

SOT-23 / SOT-113S / SOT-723			
2SK303-V2	2SK303-V3	2SK303-V4	2SK303-V5

For TO-92



■ ABSOLUTE MAXIMUM RATINGS (T_A =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		V _{DSS}	30	V
Gate to Source Voltage		V _{GSS}	-30	V
Gate Current		I _G	10	mA
Drain Current		I _D	20	mA
Power Dissipation	SOT-23	P _D	200	mW
	SOT-113S/SOT-723		100	
	TO-92		625	
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

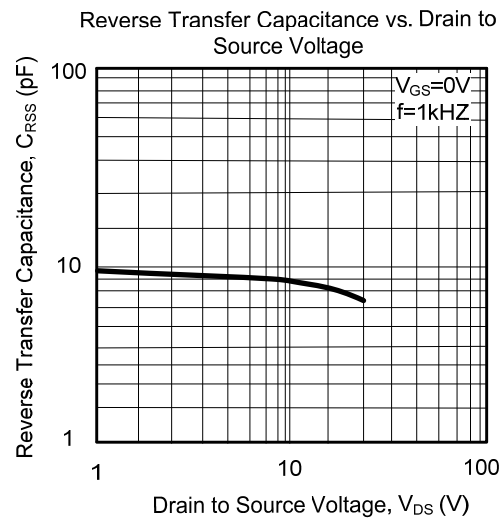
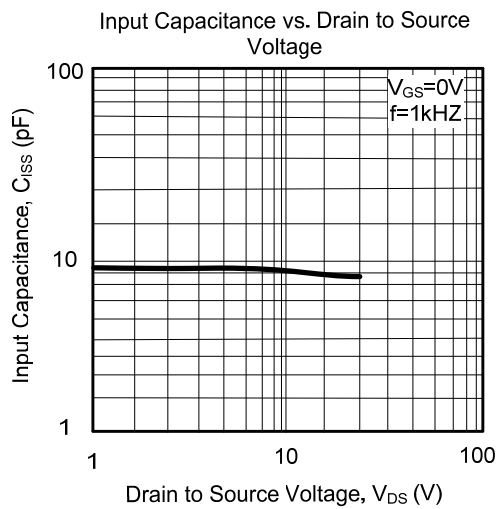
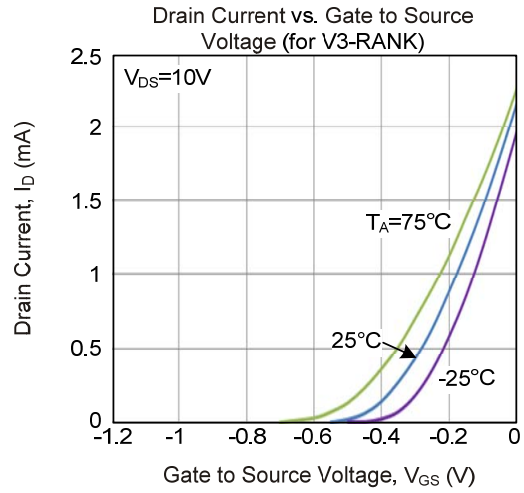
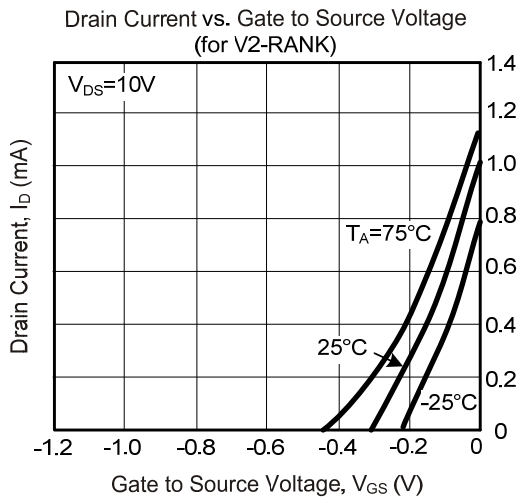
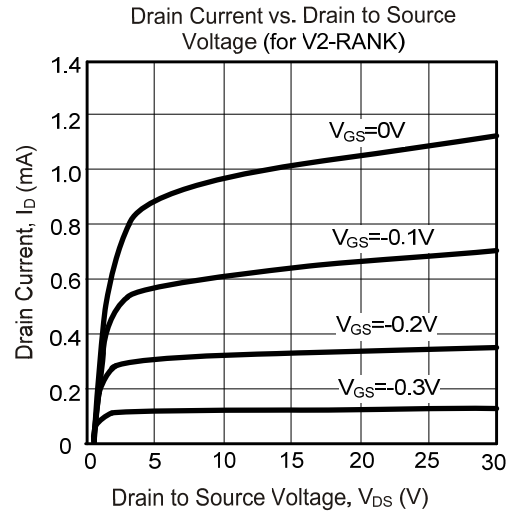
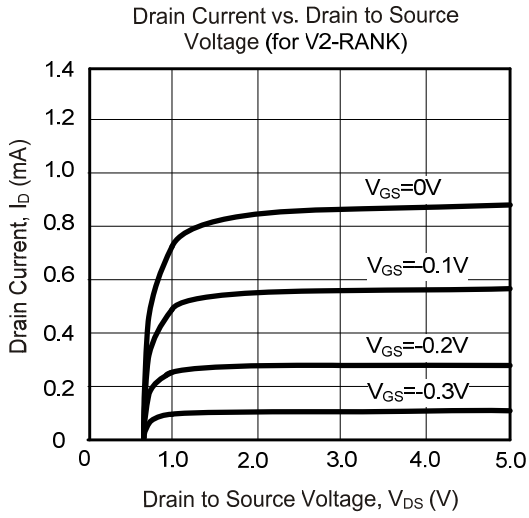
■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Gate to Drain Breakdown Voltage	BV _{GDS}	I _G =-10μA	-30			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =10V, V _{GS} =0V	0.6		12.0	mA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-20V			-1.0	nA
ON CHARACTERISTICS						
Gate Cutoff Voltage	V _{GS(OFF)}	V _{DS} =10V, I _D =1μA		-1	-4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{DS} =10mV, V _{GS} =0V		250		Ω
Forward Transfer Admittance	Y _{FS}	V _{DS} =10V, V _{GS} =0V, f =1MHz	2.5	6.0		mS
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =10V, V _{GS} =0V, f =1MHz		5		pF
Reverse Transfer Capacitance	C _{RSS}			1.5		pF

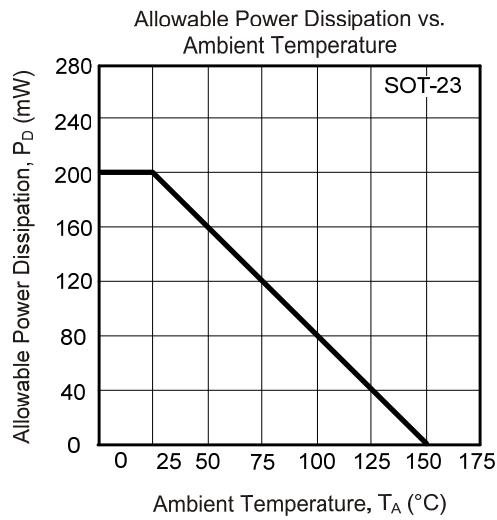
■ CLASSIFICATION OF I_{DSS}

RANK	V2	V3	V4	V5
I _{DSS} (mA)	0.6 ~ 1.5	1.2 ~ 3.0	2.5 ~ 6.0	5.0 ~ 12.0

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



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